

INFORMATION DISCLOSURE STATEMENT BY APPLICANT				<i>Complete if Known</i>	
				Application Number	New Application 10/584882
				Filing Date	Herewith
				First Named Inventor	Fariba HATAMI et al
				Group Art Unit	10584882 - GAU: 2815
				Examiner Name	Jay C. Kim
				Confirmation No.	
Sheet	1	of	4	Attorney Docket Number	3367-103

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code ² (If known)		
/J.K./	1.	6,984,850		Hiroshi Nakatsu	1/10/06
/J.K./	2.	6,936,858		Hiroshi Nakatsu†	8/30/05
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¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two-letter code. ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language translation is attached. AB indicates that only an English language abstract is attached.

INFORMATION DISCLOSURE STATEMENT BY APPLICANT				<i>Complete if Known</i>	
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FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T ²
		Office ³ Code	Number ⁴	Kind ⁵ (if known)			
/J.K./	15.	JP	08335718 (abstract only)	A	Daido Steel Co., Ltd.	12/17/96	AB
/J.K./	16.	WO	02/065520	A1	Infineon Technologies AG	8/22/02	
/J.K./	17.	WO	00/17094 (abstract only)		Fascko et al	3/30/02	AB
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/J.K./	19.	WO	99/50916	A1	Massachusetts Institute...	10/7/99	
Examiner Signature	/Jay Kim/				Date Considered	03/11/2009	

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NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
/J.K./	20.	Chen et al., "Normal-incidence voltage-tunable middle- and long-wavelength infrared photoresponse in self-assembled InAs quantum dots", APPLIED PHYSICS LETTERS, AMERICAN INSTITUTE OF PHYSICS, vol. 80, no. 14, April 8, 2002, pgs. 2490-2492.	
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	28.	F. Hatami, W. T. Masselink, L. Schrottke, J. W. Tomm, V. Talalaev, C. Kristukat, and A. R. Goni: "InP quantum dots embedded in GaP: "Optical properties and carrier dynamics", Phys. Rev. B 67, 85306-14 (2003)	
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Examiner Signature	/Jay Kim/		Date Considered 03/11/2009

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